TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

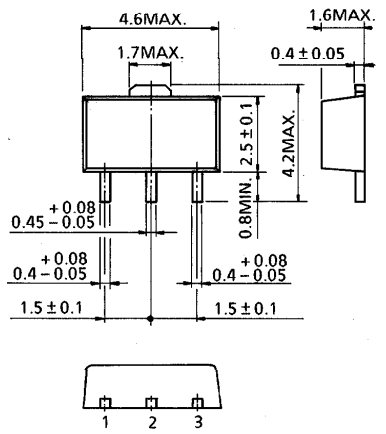
2SC2873

POWER AMPLIFIER APPLICATIONS

POWER SWITCHING APPLICATIONS

- Low Saturation Voltage : $V_{CE\ (sat)}$ = 0.5V (Max.) (I_C = 1A)
- High Speed Switching Time : t_{stg} = 1.0μs (Typ.)
- P_C = 1~2W (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to 2SA1213

Unit in mm



1. BASE
2. COLLECTOR (HEAT SINK)
3. EMITTER

JEDEC	—
EIAJ	SC-62
TOSHIBA	2-5K1A

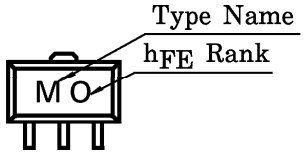
Weight : 0.05g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	2	A
Base Current	I_B	0.4	A
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation	P_C (Note)	1000	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	−55~150	°C

(Note) : Mounted on ceramic substrate (250mm²×0.8t)

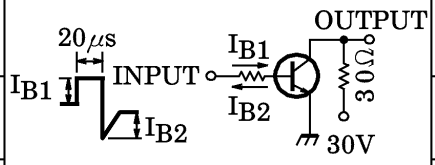
MARKING



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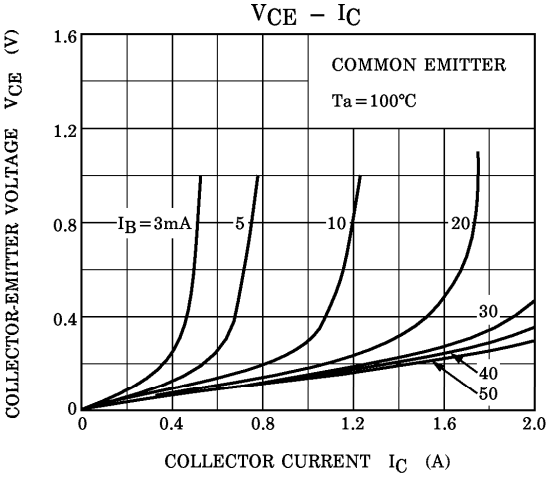
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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

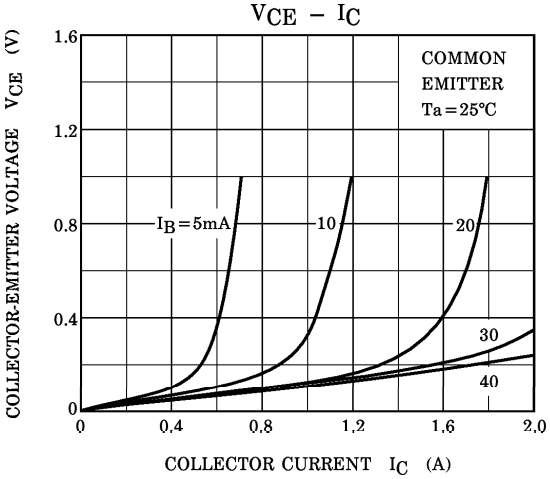
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB} = 50V, I_E = 0	—	—	0.1	μA
Emitter Cut-off Current		I_{EBO}	V_{EB} = 5V, I_C = 0	—	—	0.1	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)\,CEO}$	I_C = 10mA, I_B = 0	50	—	—	V
DC Current Gain		$h_{FE\,(1)}$ (Note)	V_{CE} = 2V, I_C = 0.5A	70	—	240	
		$h_{FE\,(2)}$	V_{CE} = 2V, I_C = 2.0A	20	—	—	
Collector-Emitter Saturation Voltage		$V_{CE\,(sat)}$	I_C = 1A, I_B = 0.05A	—	—	0.5	V
Base-Emitter Saturation Voltage		$V_{BE\,(sat)}$	I_C = 1A, I_B = 0.05A	—	—	1.2	V
Transition Frequency		f_T	V_{CE} = 2V, I_C = 0.5A	—	120	—	MHz
Collector Output Capacitance		C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	—	30	—	pF
Switching Time	Turn-on Time	t_{on}		—	0.1	—	μs
	Storage Time	t_{stg}		—	1.0	—	
	Fall Time	t_f	$I_{B1} = -I_{B2} = 0.05A$, DUTY CYCLE ≦ 1%	—	0.1	—	

(Note) : $h_{FE\,(1)}$ Classification O : 70~140, Y : 120~240

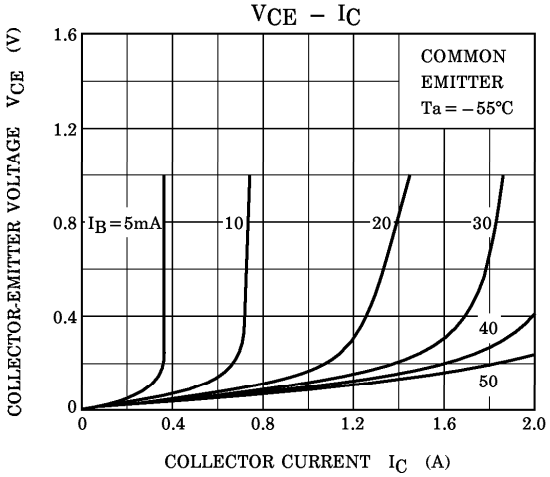
V_{CE} – I_C



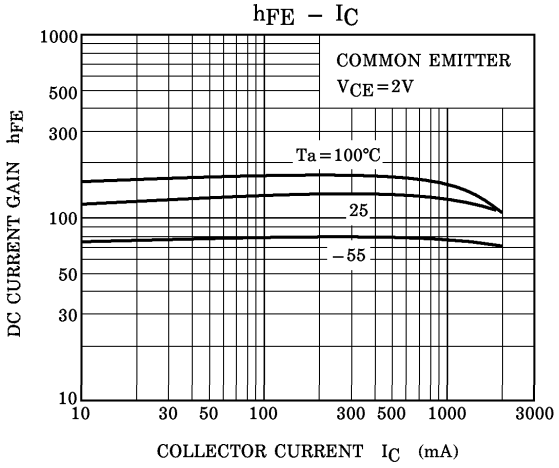
V_{CE} – I_C



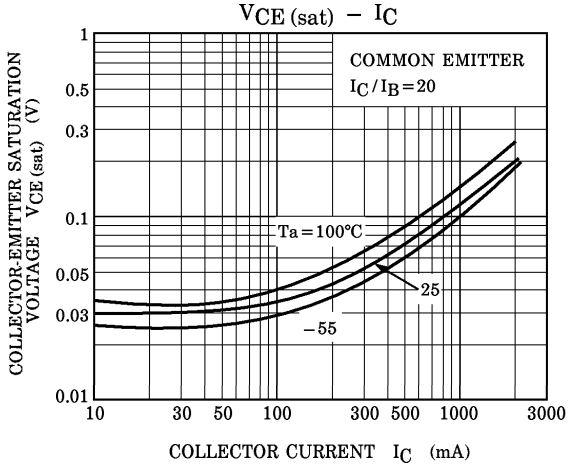
V_{CE} – I_C



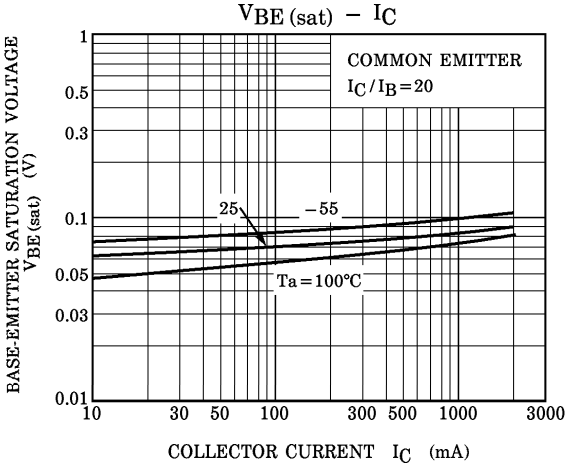
h_{FE} – I_C



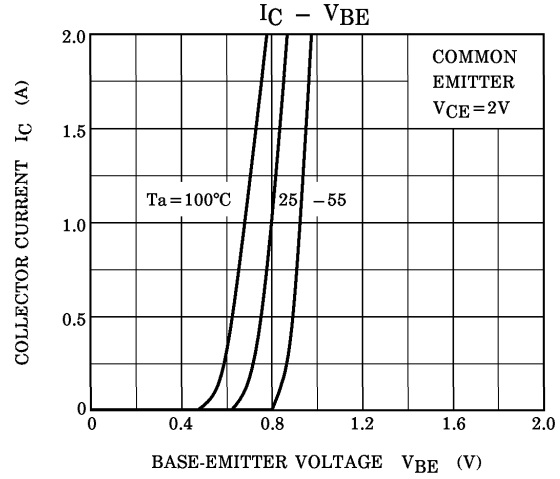
$V_{CE\,(sat)}$ – I_C



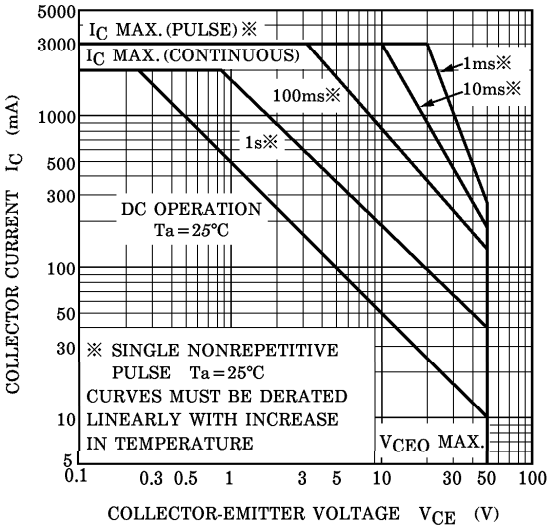
$V_{BE\,(sat)}$ – I_C



I_C – V_{BE}



SAFE OPERATING AREA



P_C – Ta

